

Silicon NPN Power Transistors

BU2515DX

DESCRIPTION

- With TO-3PML package
- High voltage
- High speed switching
- Built-in damper diode

APPLICATIONS

- For use in horizontal deflection circuits of PC monitors.

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

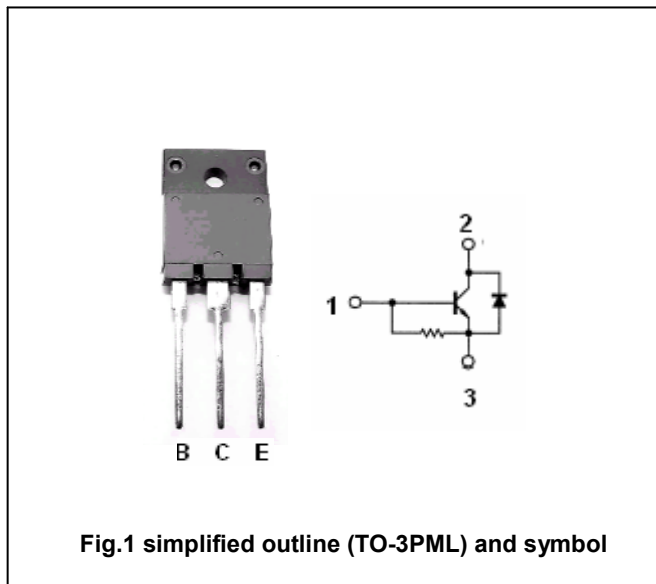


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	7.5	V
I _C	Collector current (DC)		9	A
I _{CP}	Collector current (Pulse)		20	A
I _B	Base current (DC)		5	A
I _{BM}	Base current (Pulse)		7.5	A
P _{tot}	Total power dissipation	T _C =25°C	45	W
T _j	Max.operating junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0, L=25mH	800			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =600mA ; I _C =0	7.5	13.5		V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A ; I _B =0.9A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A ; I _B =0.9A			1.0	V
I _{CES}	Collector cut-off current	V _{CE} =BV _{CEs} ; V _{BE} =0 T _C =125°C			1.0 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0		130		mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V		13		
h _{FE-2}	DC current gain	I _C =4.5A ; V _{CE} =5V	5	8	10.2	
V _F	Diode forward voltage	I _F =4.5A			2.2	V

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PACKAGE OUTLINE

